

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Rule 53(b) Divisional Application of S.N. 08/970,212:

**Shunji NAKAMURA**

Serial No.: NEW

Group Art Unit: **2811** (Expected)

Filed: **December 6, 2001**

Examiner: **NADAV, O.** (Expected)

For: **SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR FABRICATING THE SAME**

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

December 6, 2001

Sir:

Prior to calculation of the filing fee and examination of this application, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please **ADD** the following new claims 29-31:

- 1 29. (New) A semiconductor memory device comprising:
- 2 a device layer including:
- 3 a silicon layer having a first diffused region and a second diffused region formed
- 4 therein and having substantially flat surfaces, said silicon layer defining a first side and a second
- 5 side;